

The **OHTG10MRB** is a high-sensitivity NPN silicon phototransistor mounted in a T0-18 type header with black epoxy encapsulation.

With daylight filter the phototransistor is sensitive only to infraed rays.

FEATURES

- Wide angular response
- Relatively low-cost against metal can package
- Low profile package
- With daylight filter

APPLICATIONS

- Optical Switches
- Card readers
- Remote control sensors



ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25℃)

Item		Symbol	Cond.	Min.	Typ.	Max.	Unit
Collector dark current		I_{CE0}	$V_{CE0}=10V$		1	200	nA
Light current		I_L	$V_{CE}=10V, 200Lux$	0.5	1.2	5.0	mA
C-E saturation voltage		$V_{ce(sat)}$	$I_c=2mA, 2000Lux$		0.2	0.4	V
Switching speeds	Rise time	t_r	$V_{cc}=10V, I_c=5mA$ $R_L=100\Omega$		8		usec.
	Fall time	t_f			10		usec.
Spectral sensitivity		λ		720~1,050			nm
Peak wavelength		λ_p			940		nm
Half angle		$\Delta \theta$			± 70		deg.

MAXIMUM RATINGS

(Ta=25℃)

Item	Symbol	Rating	Unit
C-E voltage	V_{CE0}	40	V
E-C voltage	V_{EC0}	4	V
Collector current	I_c	30	mA
Power dissipation	P_D	100	mW
Operating temp.	$T_{opr.}$	-25~+90	℃
Storage temp.	$T_{stg.}$	-30~+100	℃
Soldering temp. ⁽¹⁾	$T_{sol.}$	260	℃

(1)For MAX.5seconds at the position of 2mm from the package

